

■ PRODUCT CHARACTERISTICS

V _{DSS}	60V
R _{DS(on)} typ(@V _{GS} = 10 V)	22.5mΩ
R _{DS(on)} typ(@V _{GS} = 4.5 V)	28mΩ
I _D	20A

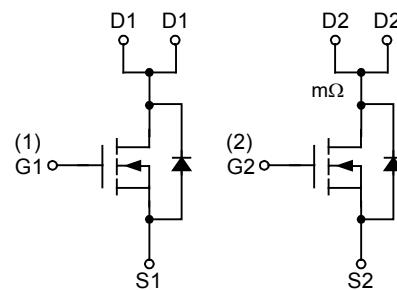
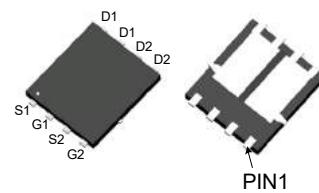
■ FEATURE

- Low R_{DS(ON)}
- Low gate charge
- Pb-free lead plating

■ APPLICATIONS

- Motor driving in power tool
- E-vehiche robotics

Pin description



N+N MOSFET

■ ORDER INFORMATION

Order codes		Package	Packing	
Halogen-free	Halogen		5000Pieces/Reel	
N/A	MOT6929J	PDFN3X3-8L		

■ ABSOLUTE MAXIMUM RATINGS (T_c = 25°C, unless otherwise specified)

Parameter	Symbol	Value	units
Drain-Source Voltage	V _{DS}	60	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	I _D	20	A
		13	A
Pulsed Drain Current	I _{DM}	80	A
Avalanche Energy	E _{AS}	13.5	mJ
Maximum Power Dissipation	P _D	28	W
		11.1	W
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 To 150	°C

■ THERMAL CHARACTERISTICS

Parameter	Symbol	Value	units
Thermal Resistance, Junction-to-Ambient	R _{θJA}	70	°C/W
Thermal Resistance, Junction-to-Case	R _{θJC}	5.2	°C/W

■ Electrical Characteristics (T_c=25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
STATIC PARAMETERS						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	I _D = 250μA, V _{GS} = 0V	60	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 48V, V _{GS} = 0V T _J = 55°C	-	-	1.0	μA
			-	-	5.0	
Gate-Body Leakage Current	I _{GSS}	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1.2	-	2.5	V
Static Drain-Source ON-Resistance	R _{DS(ON)}	V _{GS} = 10V, I _D = 5A	-	22.5	29	mΩ
		V _{GS} = 4.5V, I _D = 3A	-	28	38	mΩ
Forward Transconductance	g _{FS}	V _{DS} = 5V, I _D = 5A	-	17.0	-	S
Diode Forward Voltage	V _{SD}	I _S = 1A, V _{GS} = 0V	-	0.75	1.0	V
Diode Continuous Current	I _S	T _C = 25°C	-	-	23	A
DYNAMIC PARAMETERS						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 30V, f = 1MHz	-	288	-	pF
Output Capacitance	C _{oss}		-	92	-	pF
Reverse Transfer Capacitance	C _{rss}		-	22	-	pF
Gate Resistance	R _g	V _{GS} = 0V, V _{DS} = 0V, f = 1MHz	-	5.0	-	Ω
SWITCHING PARAMETERS						
Total Gate Charge	Q _g	V _{GS} = 0 to 10V V _{DS} = 30V, I _D = 5A	-	50	-	nC
Gate Source Charge	Q _{gs}		-	6	-	nC
Gate Drain Charge	Q _{gd}		-	15	-	nC
Turn-On Delay Time	t _{D(on)}	V _{GS} = 10V, V _{DS} = 30V R _L = 6Ω, R _{GEN} = 6Ω	-	6.0	-	nS
Turn-On Rise Time	t _r		-	62	-	nS
Turn-Off Delay Time	t _{D(off)}		-	18.5	-	nS
Turn-Off Fall Time	t _f		-	97	-	nS
Body Diode Reverse Recovery Time	t _{rr}	I _F = 5A, dI _F /dt = 100A/μs	-	13.0	-	nS
Body Diode Reverse Recovery Charge	Q _{rr}	I _F = 5A, dI _F /dt = 100A/μs	-	6.0	-	nC

■ TYPICAL CHARACTERISTICS

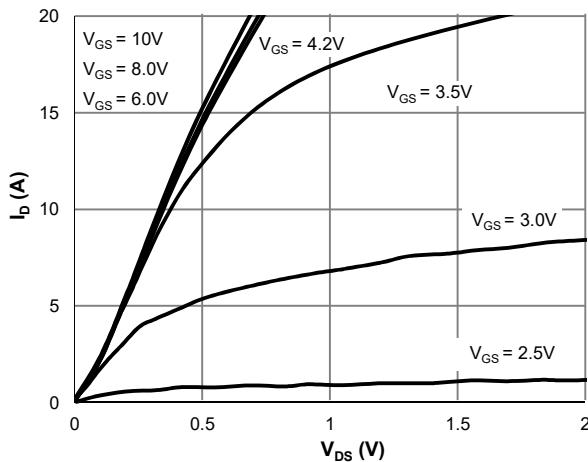


Figure 1: Saturation Characteristics

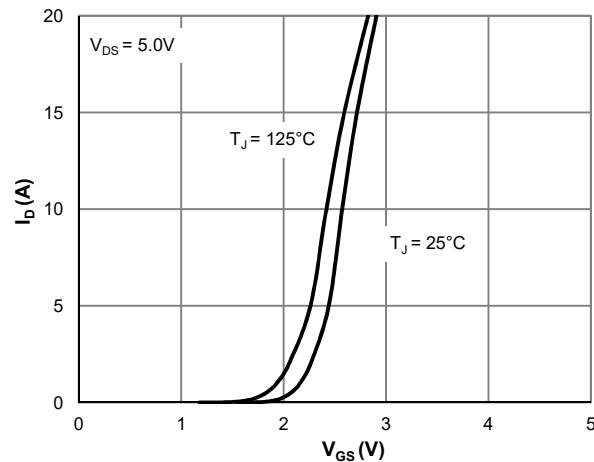
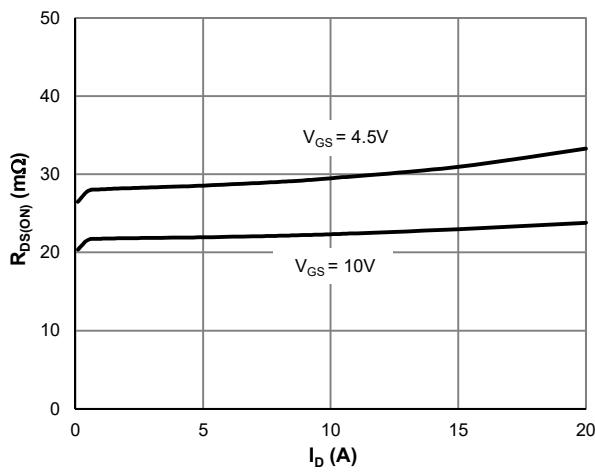
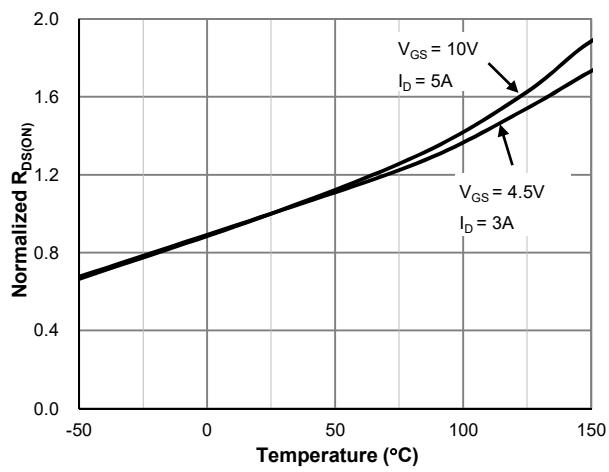
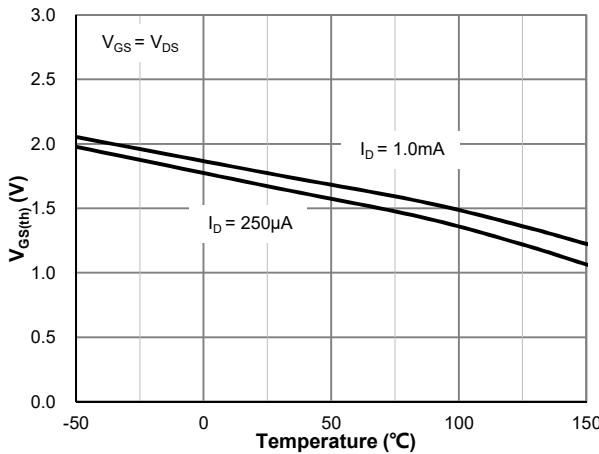
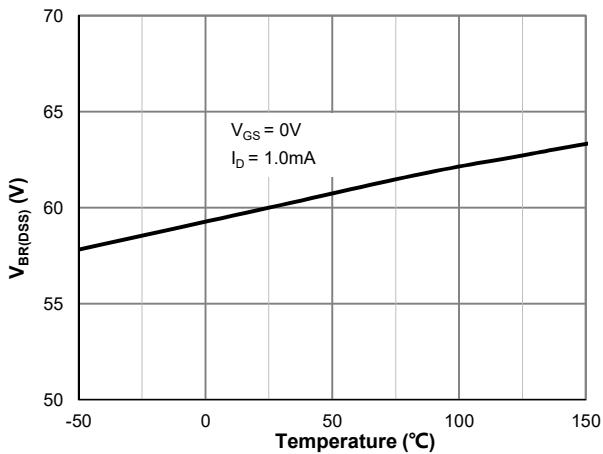


Figure 2: Transfer Characteristics

Figure 3: $R_{DS(\text{ON})}$ vs. Drain CurrentFigure 4: $R_{DS(\text{ON})}$ vs. Junction TemperatureFigure 5: $V_{GS(\text{th})}$ vs. Junction TemperatureFigure 6: $V_{BR(\text{DSS})}$ vs. Junction Temperature

■ TYPICAL CHARACTERISTICS(Cont.)

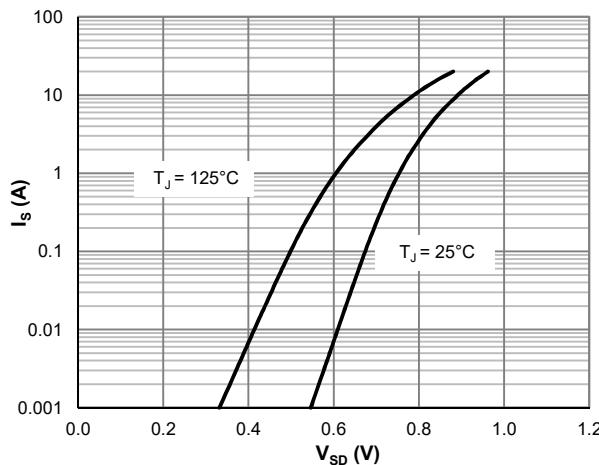


Figure 7: Body-Diode Characteristics

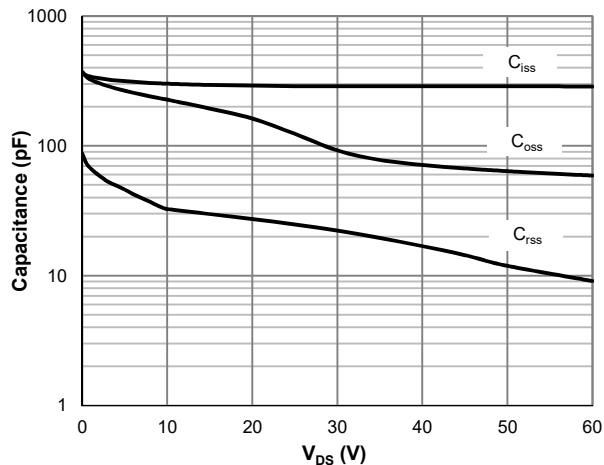


Figure 8: Capacitance Characteristics

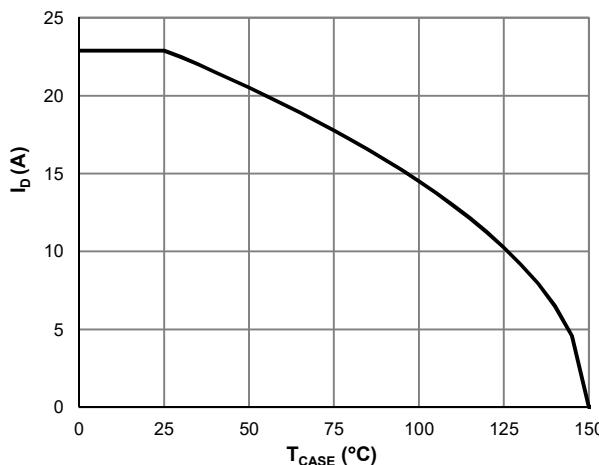


Figure 9: Current De-rating

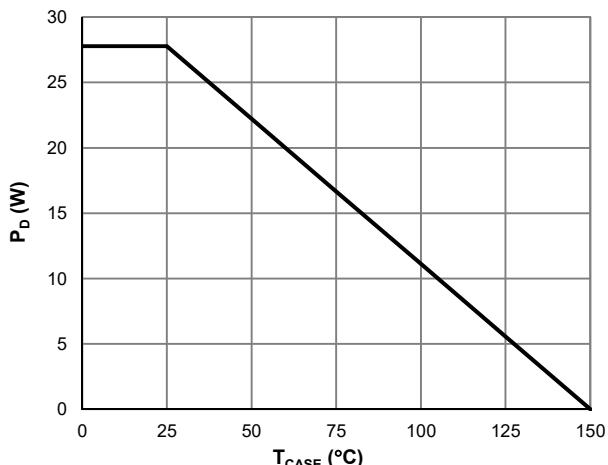


Figure 10: Power De-rating

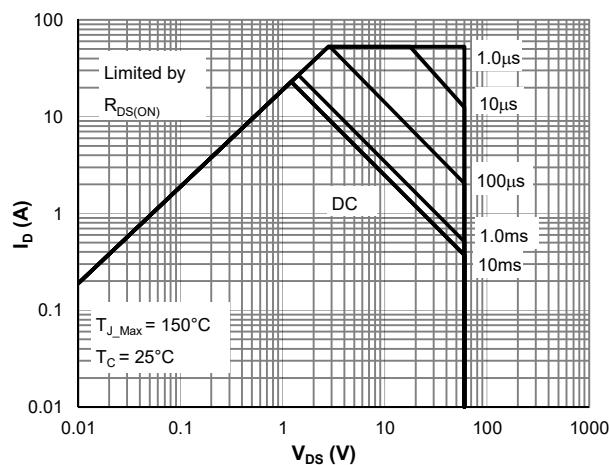
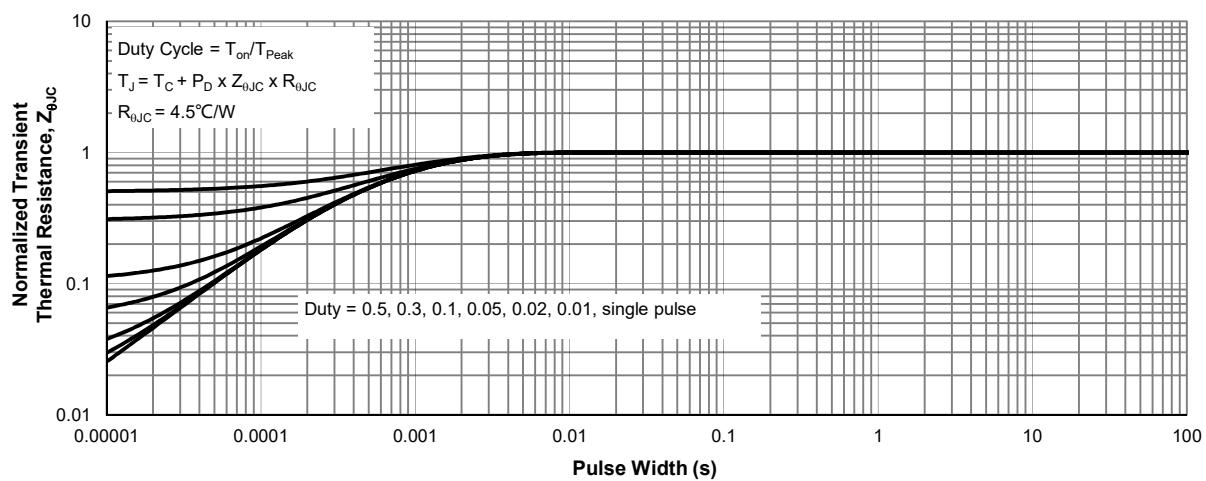
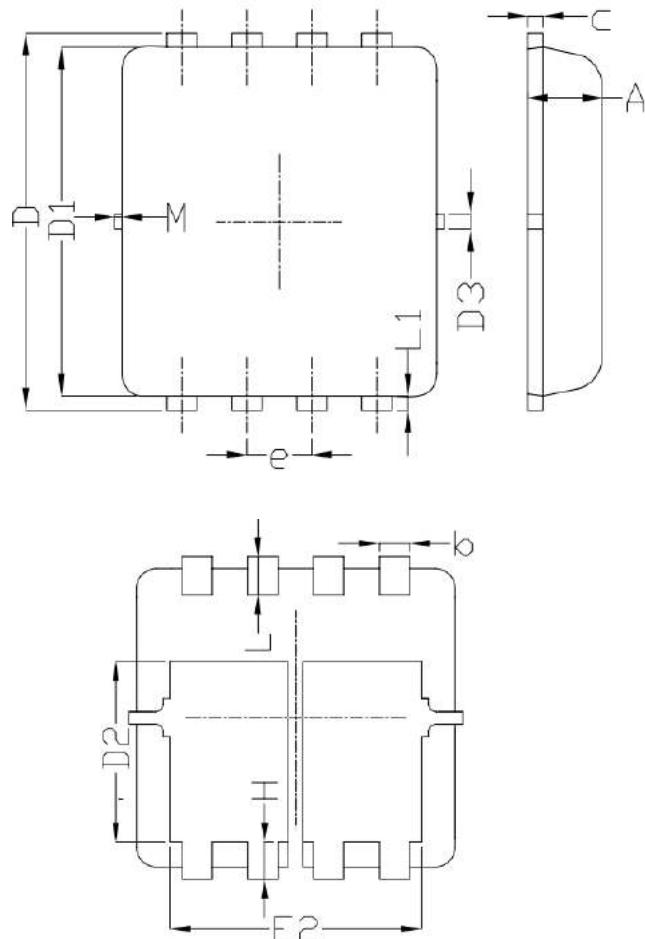


Figure 11: Maximum Safe Operating Area

■ TYPICAL CHARACTERISTICS(Cont.)

Figure 12: Normalized Maximum Transient Thermal Impedance

■ PDFN3X3-8L Package Mechanical Data



SYMBOL	DIMENSIONAL REQMTS		
	MIN	NOM	MAX
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.78	1.88	1.98
D3	---	0.13	---
E	3.20	3.30	3.40
E1	3.00	3.15	3.20
E2	2.39	2.49	2.59
e	0.65BSC		
H	0.30	0.39	0.50
L	0.30	0.40	0.50
L1	---	0.13	---
θ	---	10°	12°
M	*	*	0.15

* Not specified